

preliminary

Sonic Fast Recovery Diode

$$V_{RRM} = 1200 \text{ V}$$

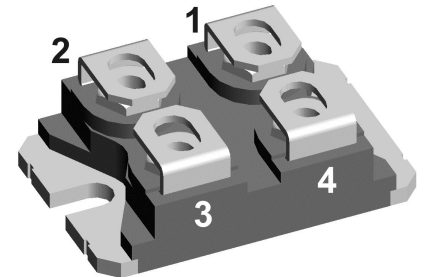
$$I_{FAV} = 2 \times 50 \text{ A}$$

$$t_{rr} = 200 \text{ ns}$$

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Parallel legs

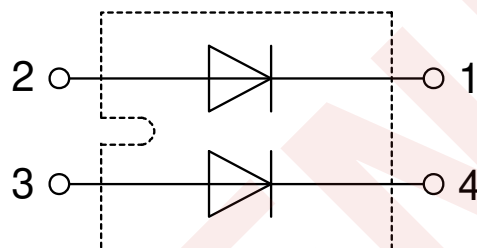
Part number

DHG100X1200NA



Backside: Isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

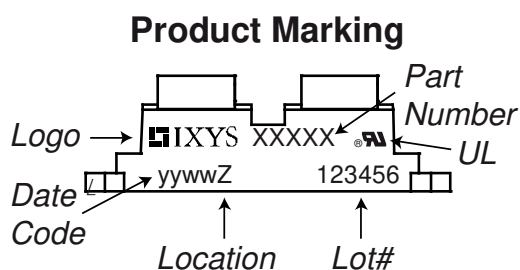
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Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V	
I _R	reverse current, drain current	V _R = 1200 V	T _{VJ} = 25°C			100	μA	
		V _R = 1200 V	T _{VJ} = 125°C			1.2	mA	
V _F	forward voltage drop	I _F = 50 A	T _{VJ} = 25°C			2.16	V	
		I _F = 100 A				2.78	V	
		I _F = 50 A	T _{VJ} = 125°C			2.13	V	
		I _F = 100 A				2.97	V	
I _{FAV}	average forward current	T _C = 65°C rectangular d = 0.5	T _{VJ} = 150°C			50	A	
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 150°C		1.26	V	
r _F	slope resistance					15.3	mΩ	
R _{thJC}	thermal resistance junction to case					0.6	K/W	
R _{thCH}	thermal resistance case to heatsink				0.1		K/W	
P _{tot}	total power dissipation	T _C = 25°C				200	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		500	A	
C _J	junction capacitance	V _R = 600 V f = 1 MHz		T _{VJ} = 25°C		27	pF	
I _{RM}	max. reverse recovery current	} I _F = 60 A; V _R = 600 V -di _F /dt = 1200 A/μs		T _{VJ} = 25 °C		45	A	
				T _{VJ} = 125 °C		60	A	
t _{rr}	reverse recovery time			T _{VJ} = 25 °C		200	ns	
				T _{VJ} = 125 °C		350	ns	



preliminary

Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				100	A
T _{VJ}	virtual junction temperature			-40		150	°C
T _{op}	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		150	°C
Weight					30		g
M _D	mounting torque			1.1		1.5	Nm
M _T	terminal torque			1.1		1.5	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}		terminal to backside	8.6	6.8			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3000			V
		t = 1 minute		2500			V



Part description

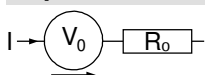
D = Diode
H = Sonic Fast Recovery Diode
G = extreme fast
100 = Current Rating [A]
X = Parallel legs
1200 = Reverse Voltage [V]
NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG100X1200NA	DHG100X1200NA	Tube	10	507759

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$

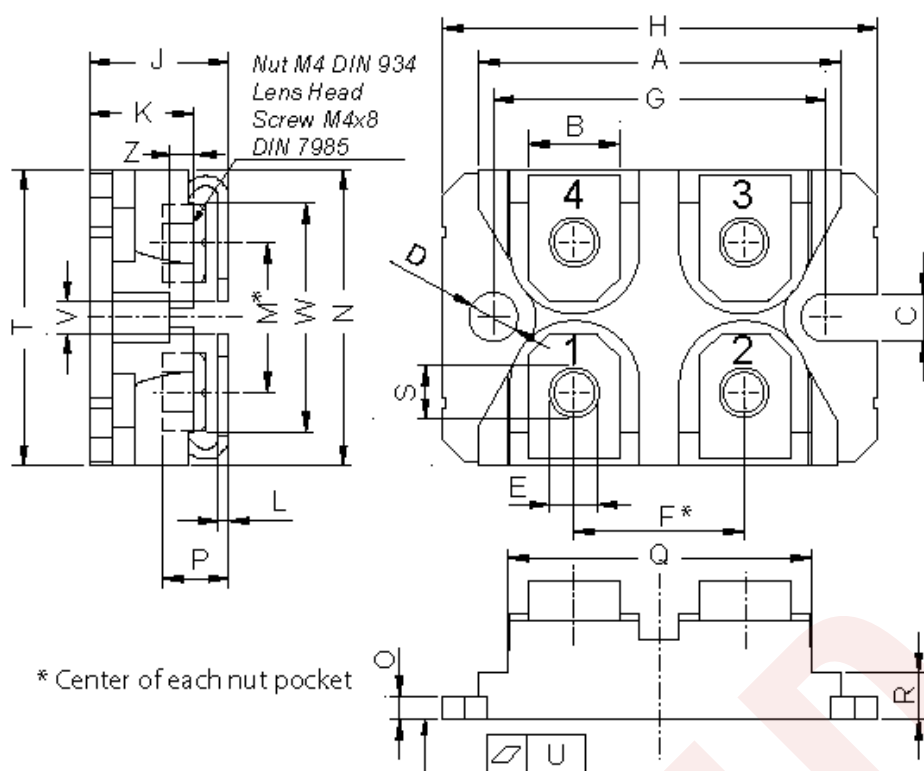


$V_{0\max}$ threshold voltage
 $R_{0\max}$ slope resistance *

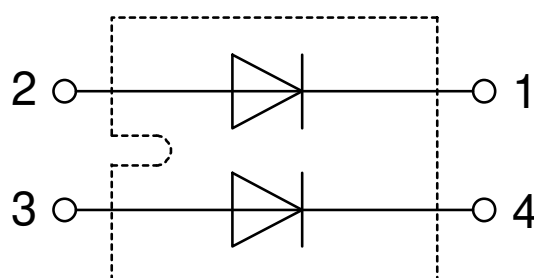
Fast Diode

1.26

V
mΩ

Outlines SOT-227B (minibloc)


Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



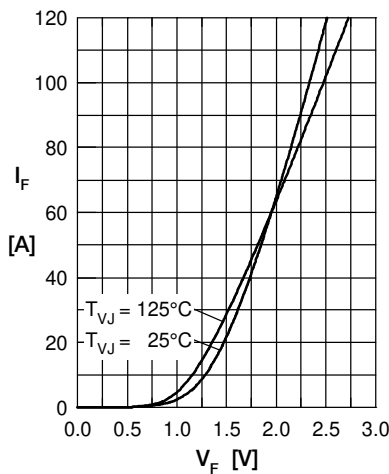
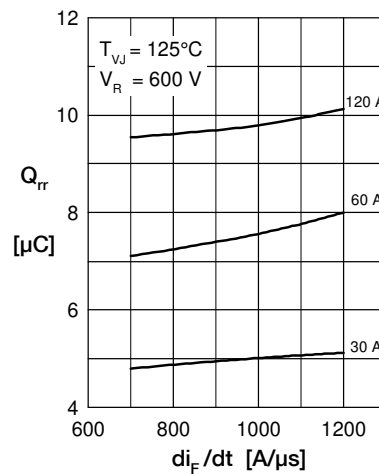
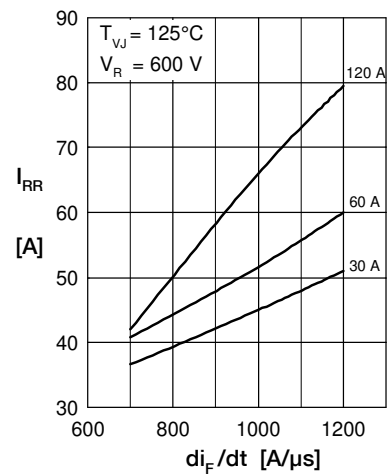
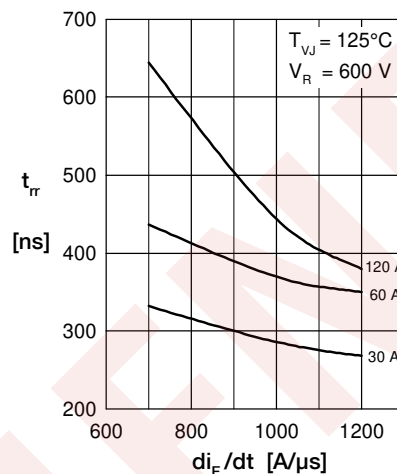
Fast Diode

 Fig. 1 Typ. Forward current versus V_F

 Fig. 2 Typ. reverse recov. charge Q_{rr} versus di_F/dt

 Fig. 3 Typ. peak reverse current I_{RM} versus di_F/dt

 Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

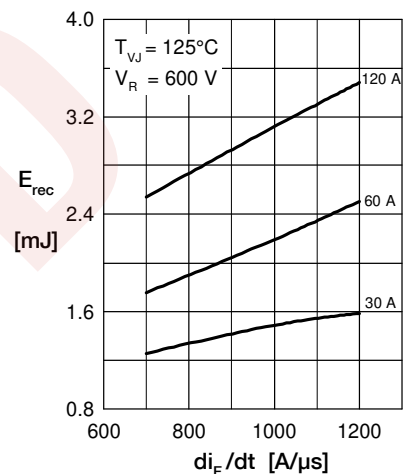
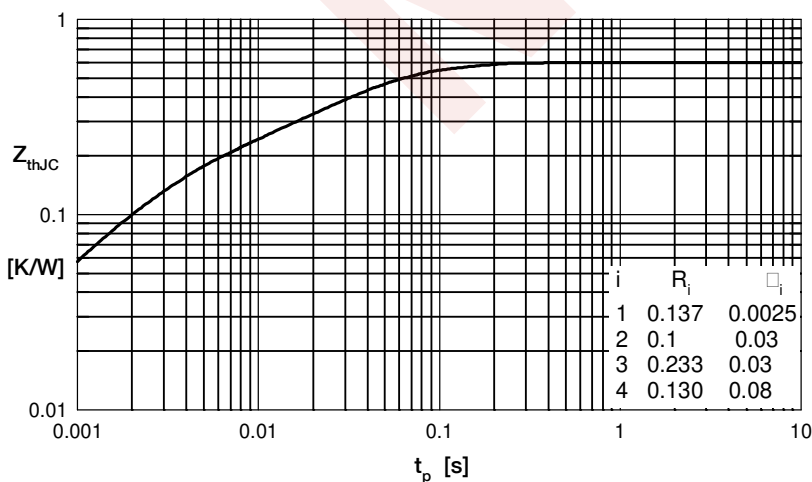
 Fig. 5 Typ. recovery time t_{rr} versus di_F/dt

 Fig. 6 Typ. recovery energy E_{rec} versus di_F/dt


Fig. 7 Typ. transient thermal impedance junction to case